

#### Dual 1-of-4 Decoder / Demultiplexer in bare die form

**Rev 1.1** 21/07/20

### Description

The 54HC139 is fabricated using a 2.5µm 5V CMOS process and has the same high speed performance of LSTTL combined with CMOS low power consumption. This device consists of x2 independent 1-of-4 decoders, each decoding a 2 bit address to 1-of-4 active-low outputs. Active-low Selects facilitate the demultiplexing and cascading functions. The demultiplexing function is executed by using the Address inputs to select the desired device output and utilizing the Select as a data input.

Features:

- Output Drive Capability: 10 LSTT
- Low Input Current: 1µA
- Outputs directly interface CNCS NMOS and TTL
- Operating Voltage Range: 2% to 6V
- CMOS High Noise Impunity
- Function compatible with 54LS139
- Full Military Temperature Range.

### **Ordering Information**

The following part suffixes apply:

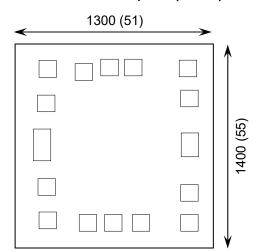
- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection Space) + MIL-PRF-38534 Class k

LAT = Lot Acceptance Test.

For further information on L ss flows see below.

www.siliconsupplies.com\qua bare-die-lot-qualification

### ensions in µm (mils)



### Supply Formats

- Defact Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

### **Mechanical Specification**

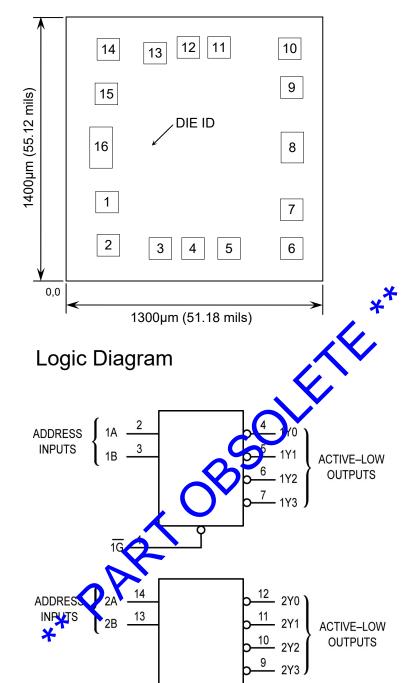
Die Size (Unsawn)	1300 x 1400 51 x 55	µm mils	
Minimum Bond Pad Size	106 x 106 4.17 x 4.17	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	µm mils	
Top Metal Composition	Al 1%Si 1.1μ	m	
Back Metal Composition	N/A – Bare Si		





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### Pad Layout and Functions



PAD	FUNCTION	COORDIN	ATES (mm)					
FAD	TONCTION	Х	Y					
1	1G	0.152	0.366					
2	1A	2.162	0.132					
3	1B	0.422	0.122					
4	11/6	0.59	0.122					
5	1Y	0.772	0.122					
6	1Y2	1.088	0.122					
7	1Y3	1.088	0.333					
В	GND	1.088	0.619					
9	2Y3	1.088	0.972					
10	2Y2	1.078	1.173					
11	2Y1	0.722	1.183					
12	2Y0	0.566	1.183					
13	2B	0.396	1.153					
14	2A	0.162	1.173					
15	2G	0.152	0.938					
16	V <sub>CC</sub>	0.122	0.591					
CON	CONNECT CHIP BACK TO V <sub>CC</sub> OR FLOAT							

### **Truth Table**

IN	IPUTS			OU	TPUTS	S
G	В	Α	Y0	Y1	Y2	Y3
Н	Х	Χ	Н	Н	Н	Н
L	L	L	L	Н	Н	Н
L	L	Н	H	L	Н	Н
L	Н	L	H	Н	L	Н
L	Н	Н	Н	Н	Н	L

X = don't care



2G \_\_\_\_\_\_15

Pad  $16 = V_{CC}$ Pad 8 = GND



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## Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V <sub>CC</sub>	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V <sub>IN</sub>	-1.5 to V <sub>CC</sub> +1.5	<b>Y</b> ,
DC Output Voltage (Referenced to GND)	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> +0.5	
DC Input Current, per pin	I <sub>IN</sub>	±20	mA
DC Output Current, per pin	I <sub>OUT</sub>	±25	mA
DC V <sub>CC</sub> or GND Current, per pin	I <sub>CC</sub>	±50	mA
Power Dissipation in Still Air <sup>2</sup>	P <sub>D</sub>	750	mW
Storage Temperature Range	T <sub>STG</sub>	-65,0 150	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on the att. ch and assembly method.

### Recommended Operating Conditions<sup>3</sup> (Voltages reprended to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage		V <sub>CC</sub>	<b>x</b> 2	6	V
DC Input or Output Voltage	V <sub>IN</sub> ,V <sub>OUT</sub>	<b>*</b> 0	V <sub>CC</sub>	V	
Operating Temperature Rar	TJ	-55	+125	°C	
	V <sub>CC</sub> = 2.0V		/ 0	1000	
Input Rise and Fall Time	V <sub>CC</sub> = 4.5V	t <sub>r</sub> , t <sub>f</sub>	0	500	ns
	V <sub>CC</sub> = 6.0V		0	400	

<sup>3.</sup> This device contains protection circuitry to guard equins damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{IN}$  and  $V_{OUT}$  should be constrained to the range GND  $\leq$  ( $V_{IN}$  or  $V_{CC}$ ). Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

### DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V <sub>cc</sub> CONDITIONS	LIMITS			UNITS	
TANAMETER			CONDITIONS	25°C	85°C	FULL RANGE⁴	514110
Minimum High Lovel Input Votage		2.0V	V <sub>OUT</sub> = 0.1V or	1.5	1.5	1.5	
	V <sub>IH</sub>	4.5V	V <sub>CC</sub> -0.1V   I <sub>OUT</sub>   ≤ 20µA	3.15	3.15	3.15	V
		6.0V		4.2	4.2	4.2	
Maximum Low-Level Input Voltage	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	2.0V	V <sub>OUT</sub> = 0.1V or	0.5	0.5	0.5	
		4.5V	V <sub>CC</sub> -0.1V	1.35	1.35	1.35	V
		6.0V	I <sub>OUT</sub>   ≤ 20μA	1.8	1.8	1.8	

**<sup>4.</sup>**  $-55^{\circ}C \le T_{J} \le +125^{\circ}C$ 





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### DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V <sub>cc</sub> CONDITIONS		LIMITS			UNITS
T / II V III E I E I		1111202	CONSTITUTION	25°C	85°C	FULL RANGE⁴	
		2.0V		1.9	1.9	1.9	
		4.5V		4.4	4.4	4.4	
Minimum High-Level		6.0V	1.0011 = 11.1	5.9	5.9	5.2	
Output Voltage	V <sub>OH</sub>	4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 4.0 \text{mA}$	3.98	3.84	3.₹0	V
		6.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 5.2 \text{mA}$	5.48	5.34	5.20	
	V <sub>OL</sub> 4.5V	2.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT}  \le 20\mu\text{A}$	0.1	.1	0.1	
		4.5V		0.1	0.1	0.1	
Maximum Low-Level		6.0V	1 0011	0.1	<b>3.1</b>	0.1	
Output Voltage		4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 4.0 \text{mA}$	2.26	0.33	0.40	V
		6.0V	$\begin{array}{c c} V_{\text{IN}} = V_{\text{IH}} \text{ or } V_{\text{IL}} \\  I_{\text{OUT}}  \leq 5.2 \text{mA} \end{array}$	0.26	0.33	0.40	
Maximum Input Leakage Current	I <sub>IN</sub>	6.0V	V <sub>IN</sub> = V <sub>CC</sub> or SND	±0.1	±1.0	±1.0	μΑ
Maximum Quiescent Supply Current	I <sub>CC</sub>	6.0V	V <sub>IN</sub> = V <sub>CC</sub> or GND	4	40	160	μΑ

## AC Electrical Characteristics

DADAMETED	SYMBOL		CONDITIONS		LIMITS		
PARAMETER	STWIBUL	CONDITIONS	25°C	85°C	FULL RANGE⁴	UNITS	
Maximum		2.0V	0 - 50-5	115	145	175	
Propagation Delay, Select to Output Y	t <sub>PLI</sub> , t <sub>HL</sub>	4.5V	$C_L = 50pF,$ $t_r = t_f = 6ns$	23	29	35	ns
(Figure 1, 3)	$\bigcirc$	6.0V	4 4 55	20	25	30	
Maximum		2.0V		115	145	175	
Propagation Delay, Input A to Output	t <sub>PLH</sub> , t <sub>PHL</sub>	4.5V	$C_L = 50pF,$ $t_r = t_f = 6ns$	23	29	35	ns
(Figure 2.3)		6.0V	- t <sub>f</sub> - t <sub>f</sub> - 0113	20	25	30	
Maximum O kput		2.0V	0 50 5	75	95	110	
Transtion Time, Any Output	t <sub>TLH,</sub> t <sub>THL</sub>	4.5V	$C_L = 50pF,$ $t_r = t_f = 6ns$	15	19	22	ns
(Figure 1,3)		6.0V		13	16	19	
Maximum Input Capacitance	C <sub>IN</sub>	-	-	10	10	10	pF
Power Dissipation	_		T <sub>J</sub> = 25°C,		TYPI	CAL	
Capacitance (Per Decoder) <sup>7</sup>	C <sub>PD</sub>	-	$V_{CC} = 5.0V$		5	5	pF

<sup>6.</sup> Not production tested in die form, characterized by chip design and tested in package.



<sup>7.</sup> Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .



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### **Pad Description**

**ADDRESS INPUTS** 

1A, 1B, 2A, 2B

(Pads 2, 3, 14, 13)

When the respective 1-of-4 decoder is enabled these inputs determine which of its four active-low outputs is selected

#### **CONTROL INPUTS**

1G, 2G

(Pads 1, 15)

Active—low select inputs. For a low level on this input, the outputs for that particular decoder follow the ddiess inputs. A high level on this input forces all outputs to a high level.

#### **OUTPUTS**

1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3

(Pads 4-7, 12, 11, 10, 9)

Active—low outputs. These outputs assume a low level when addressed and the appropriate select input is active. These outputs remain high when not addressed or the appropriate Select input is inactive.

### **Switching Waveforms**

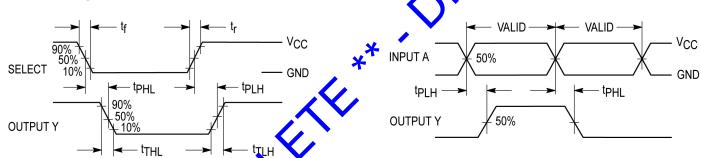
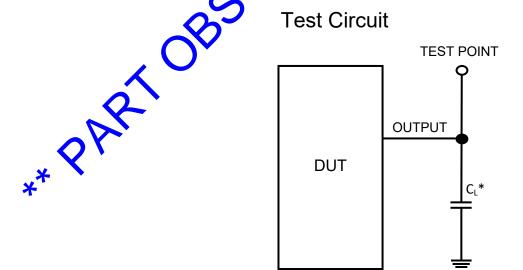


Figure 1 Figure 2



<sup>\*</sup> Includes all probe and jig capacitance





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